

Silicon Flip Zener Diode

PSZ-1056026F-13V

Description

- PSZ-1056026F-13V is silicon planar Zener Diode for Flip Bonding.
- Lateral P/N/P type.

Application

- ESD & Surge Protector for LEDs

Feature

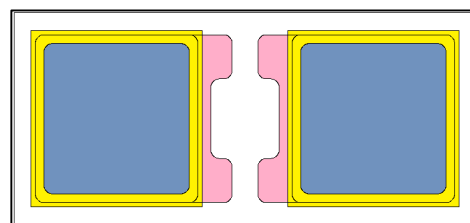
- **Chip Size** : $540(\pm 20)\mu\text{m} \times 240(\pm 20)\mu\text{m}$
- **Chip Thickness** : $100\mu\text{m} \pm 15\mu\text{m}$
- **Structure** : Lateral P/N/P

- **Metallization**

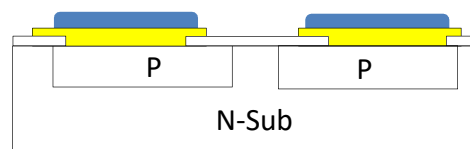
- > **Top**

- Diffusion Barrier : Gold(Au)
 - Solder : Gold-Tin(Au/Sn) 3um

- > **Bottom** : None



[Top View]



[Cross Section]

- **Bonding Pad Size**

- Diffusion Barrier : □ $200\mu\text{m} \times 200\mu\text{m}$
 - Solder : □ $190\mu\text{m} \times 190\mu\text{m}$
 - Distance of Pad to Pad : $100\mu\text{m}$

Electrical and Optical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Zener Voltage	$V_{Z(F)}$	$I_F = 5\text{mA}$	11	13	15	V
Reverse Zener Voltage	$V_{Z(R)}$	$I_Z = 5\text{mA}$	11	13	15	V
Forward Current	I_F	$V_F = 8\text{V}$			0.1	μA
Reverse Current	I_R	$V_R = 8\text{V}$			0.1	μA

Absolute Maximum Rating (Ta=25°C)

Parameter	Symbol	Maximum Rating	Unit
Power dissipation	P_d	100	mW
Junction Temperature	T_j	150	°C